

WPH4003-1E Datasheet



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DiGi Electronics Part Number WPH4003-1E-DG

Manufacturer onsemi

Manufacturer Product Number WPH4003-1E

Description MOSFET N-CH 1700V 2.5A TO3PF

Detailed Description N-Channel 1700 V 2.5A (Tc) 3W (Ta), 55W (Tc) Throu

gh Hole TO-3PF



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
WPH4003-1E	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
1700 V	2.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	10.50hm @ 1.5A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
	48 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	850 pF @ 30 V
FET Feature:	Power Dissipation (Max):
	3W (Ta), 55W (Tc)
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-3PF	TO-3P-3 Full Pack
Base Product Number:	
WPH4003	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

Ordering number : ENA1967A

WPH4003

ON Semiconductor®

N-Channel Power MOSFET 1700V, 3A, 10.5Ω, TO-3PF-3L

http://onsemi.com

Features

- ON-resistance RDS (on) = 8.2Ω (typ.)
- Input Capacitance Ciss=850pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		1700	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only maximum temperature Tch=150°C	3	Α
Drain Current (DC)	I _{Dpack*2}	Tc=25°C (Our ideal heat dissipation condition) *3	2.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	6	Α
Alle alle De la Bioline	Do		3.0	W
Allowable Power Dissipation	PD	Tc=25°C	55	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		49	mJ
Avalanche Current *5	IAV		3	А

Note:*1 Shows chip capability

- *2 Package limited
- *3 Our condition is radiation from backside.

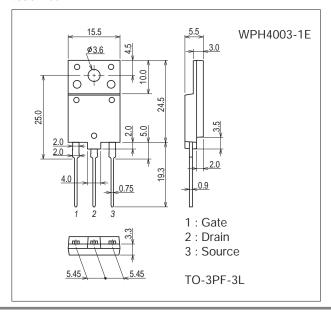
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=50V, L=10mH, IAV=3A (Fig.1)
- *5 L≤10mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7538A-002



Product & Package Information

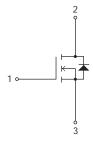
Package : TO-3PF-3LJEITA, JEDEC : SC-96

• Minimum Packing Quantity: 30 pcs./magazine

Marking

Electrical Connection





Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	1700			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1360V, V _{GS} =0V			1	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2		4	V
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1.5A	1.2	2.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =1.5A, V _G S=10V		8.2	10.5	Ω
Input Capacitance	Ciss			850		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss			27		pF
Turn-ON Delay Time	t _d (on)			19		ns
Rise Time	t _r	Son Fig 2		21		ns
Turn-OFF Delay Time	t _d (off)	See Fig.2		200		ns
Fall Time	t _f			55		ns
Total Gate Charge	Qg			48		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =3A		6		nC
Gate-to-Drain "Miller" Charge	Qgd			22		nC
Diode Forward Voltage	V _{SD}	IS=3A, VGS=0V		0.8	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		410		ns
Reverse Recovery Charge	Q _{rr}	IS=3A, VGS=0V, di/dt=100A/μs		3000		nC

Fig.1 Unclamped Inductive Switching Test Circuit

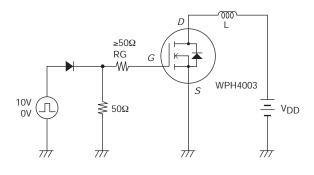


Fig.2 Switching Time Test Circuit

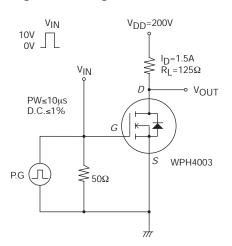
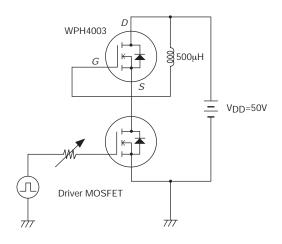
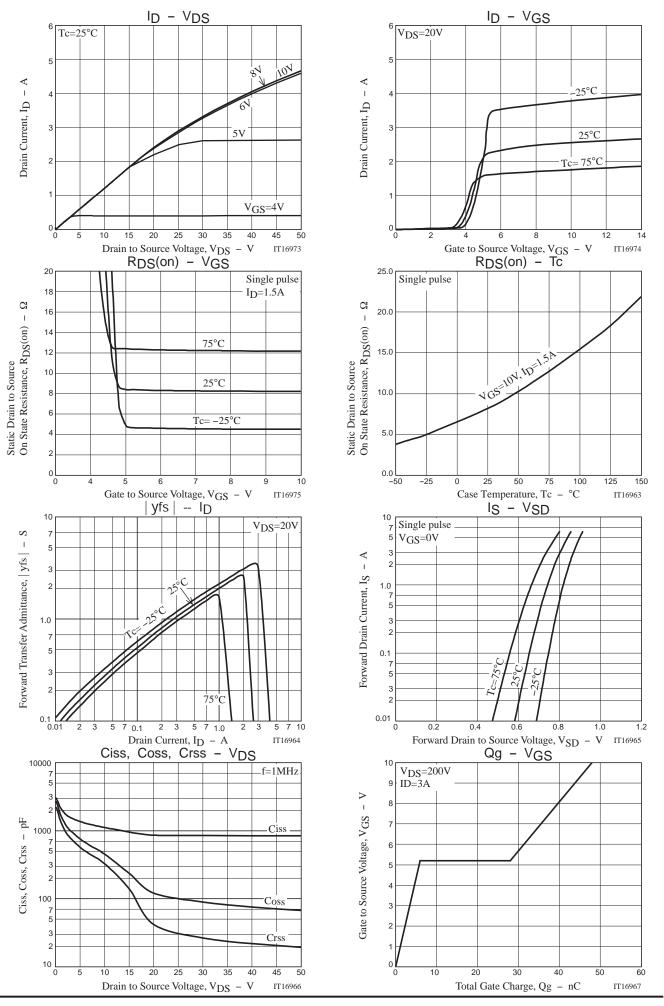


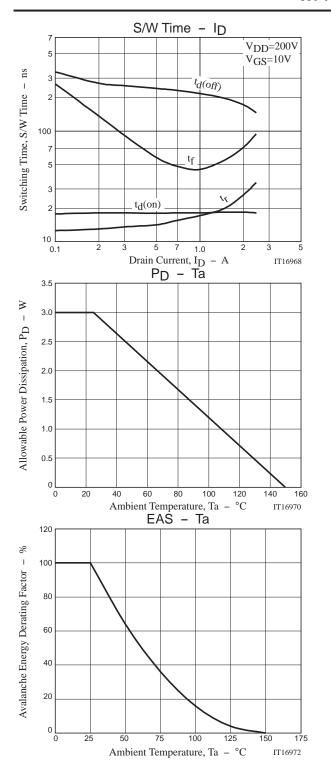
Fig.3 Reverse Recovery Time Test Circuit

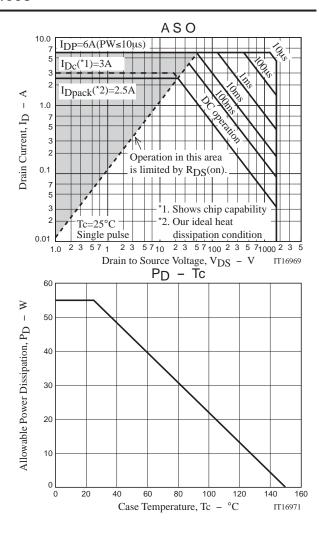


Ordering Information

Device	Package	Shipping	memo	
WPH4003-1E	TO-3PF-3L	30pcs./magazine	Pb Free	





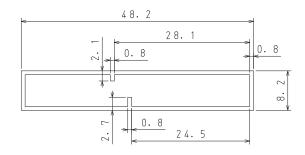


Magazine Specification

WPH4003-1E

1. Packing Format

Maximum Number of Packing format Package Name				format	
I wonaso Mamo	Magazine	Inner box	Outer box	Inner BOX	Outer BOX
:0-3PF-3L	30	360	1440		SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178



Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

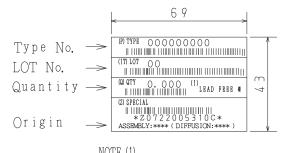
3. Storage method to magazine

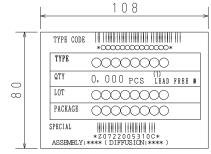


4. Inner box label (unit:mm)

5. Outer box label (unit:mm)

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



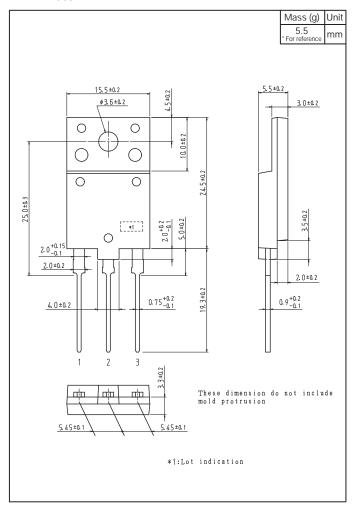


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

WPH4003-1E



Note on usage: Since the WPH4003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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